

Application No.: 10/074,151  
Docket No.: JCLA5041-CA2

**IN THE SPECIFICATION:**

*Please replace the paragraph beginning at page 1, line 4 with the following rewritten paragraph:*

B1  
--This application is a continuation application of, and claims the priority benefit of, U.S. application serial No. ~~09/77,583~~ 09/777,583 filed on February 6, 2001, which in turn is a continuation application of U.S. application serial No. 09/417,357 filed on October 13, 1999, now US Patent No. 6,254,739.--

*Please replace the paragraph beginning at page 6, line 5 with the following rewritten paragraph:*

B2  
--Specifically, when the dry surface treatment is implemented, two power supplies 302, 304 are separately provided to the argon and the heater 310 (also substrate electrode). The power provided to the substrate electrode 310 causes the substrate 300 to acquire a self-bias, and thereby accelerates argon ions from the target 310 toward the exposed substrate 300 and polysilicon gate. Thus, the exposed substrate 300 and polysilicon gate are subject to some bombardment by the argon ions 308 from the target 310. The argon is preferably provided with a bias of about 250W to about 450W from the first power supply 302, while the substrate 300 is preferably provided with a bias of about 150W to about 300W from the second power supply 304. 450W is an upper limit provided to a conventional IMP chamber, but the upper limit is variable according to the development of plasma equipment. Preferably, the bias provided from the first power supply 302 is substantially higher than the bias provided from the second power supply 304. By properly modifying the quantities of the RF power, the substrate bias and the substrate position (preferably on the heater), this dry surface treatment can be harnessed to simultaneously amorphize and clean the exposed substrate 300 and polysilicon gate.--

*Please replace the paragraph beginning at page 7, line 9 with the following rewritten paragraph:*

B3  
--Subsequent to the dry surface treatment, Titanium (Ti) or cobalt (Co) deposition step

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B3  
contd

450a can be performed in the same chamber or performed in different chamber as used in the dry surface treatment. In Fig. 2, step 450a and step 445 are enclosed by a dotted line 440 to represent that they can be performed in the same chamber. This in situ deposition step 450a saves the venting/pumping time of chamber replacement, thereby improving the production throughput. --

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